4V Drive Pch MOSFET RSL020P03

●Structure

Silicon P-channel MOSFET

● Features

- 1) Low On-resistance.
- 2) High speed switching.

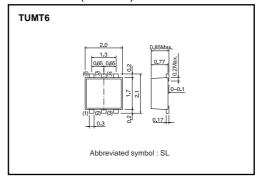
Applications

Switching

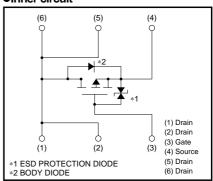
Packaging specifications

	Package	Taping	
Type	Code	TR	
	Basic ordering unit (pieces)	3000	
RSL020P03		0	

● **Dimensions** (Unit: mm)



•Inner circuit



● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	-30	V	
Gate-source voltage		Vgss	±20	V	
Drain augrant	Continuous	lσ	±2	Α	
Drain current	Pulsed	IDP *1	±8	Α	
Source current	Continuous	Is	-0.8	Α	
(Body diode)	Pulsed	Isp *1	-8	Α	
Total power dissipation		Pp *2	1	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

^{*1} Pw≤10µs, Duty cycle≤1% *2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	125	°C/W

^{*} Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	±10	μΑ	Vgs= ±20V, Vps=0V
Drain-source breakdown voltage	V _(BR) DSS	-30	_	_	V	$I_D = -1 \text{mA}, V_{GS} = 0 \text{V}$
Zero gate voltage drain current	IDSS	-	_	-1	μΑ	V _{DS} = -30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	-1.0	_	-2.5	V	V_{DS} = -10V, I_{D} = -1mA
Static drain-source on-state resistance		_	80	120	mΩ	I _D = -2A, V _G S= -10V
	R _{DS} (on)*	_	125	190	mΩ	I _D =-1A, V _{GS} = -4.5V
		_	140	210	mΩ	I _D = -1A, V _G S= -4.0V
Forward transfer admittance	Y _{fs} *	1.4	_	_	S	V _{DS} = -10V, I _D = -1A
Input capacitance	Ciss	_	350	_	pF	V _{DS} = -10V
Output capacitance	Coss	_	80	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	50	_	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	11	_	ns	V _{DD} ≒ −15V
Rise time	tr *	-	11	_	ns	I _D = -1A V _G s= -10V
Turn-off delay time	t _{d (off)} *	_	35	_	ns	$R_{L}=15\Omega$
Fall time	t _f *	-	11	_	ns	R _G =10Ω
Total gate charge	Qg	-	3.9	-	nC	V _{DD} ≒-15V V _{GS} =-5V
Gate-source charge	Qgs	_	1.3	-	nC	ID=-2A
Gate-drain charge	Q_{gd}	_	1.1	_	nC	$R_L=7.5\Omega$ $R_G=10\Omega$

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	-	_	-1.2	V	I _S = -0.8A, V _{GS} =0V

•Electrical characteristics curves

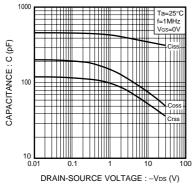


Fig.1 Typical Capacitance vs. Drain-Source Voltage

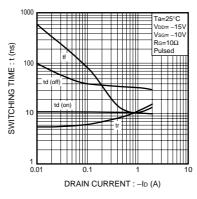


Fig.2 Switching Characteristics

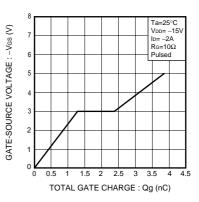


Fig.3 Dynamic Input Characteristics

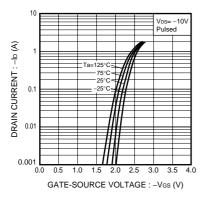


Fig.4 Typical Transfer Characteristics

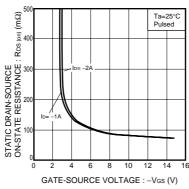


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

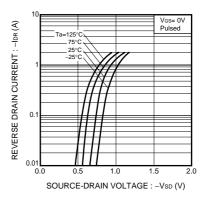


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

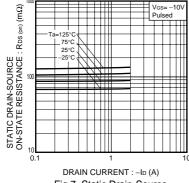
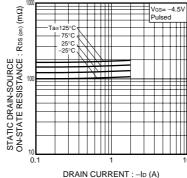
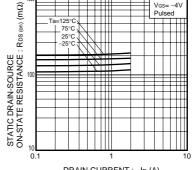


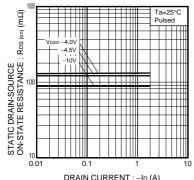
Fig.7 Static Drain-Source
On-State Resistance vs.
Drain current (I)



DRAIN CURRENT : -ID (A)
Fig.8 Static Drain-Source
On-State Resistance vs.
Drain current (II)



DRAIN CURRENT: -ID (A)
Fig.9 Static Drain-Source
On-State Resistance vs.
Drain current (III)



DRAIN CURRENT: -Io (A)
Fig.10 Static Drain-Source
On-State Resistance vs.
Drain current (IV)

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